

Amendments to the Drawings:

Please make the following changes to the Figures, as shown in the accompanying replacement sheets.

In Figure 2: Please replace “FIG. 2” with --FIG. 2a--.

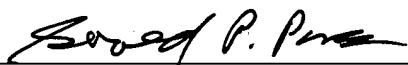
In Figure 4: Please replace “PROGRAM”, “READ”, and “ERASE” at 345 with --E--, --R--, and --PV--, add --V_R-- and --V_{PV}--, and --OTHER— at 346, and delete reference numbers 147, 203, and 347.

In Figure 5, please delete reference numbers 138, 411, 403, 421, 423, and 571.

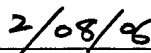
REMARKS

These remarks are in response to the telephone call from the Examiner on December 6, 2006, requesting a number of changes be made to the specification and figures of the present application. The subject of telephone call related entirely to a number changes the Examiner felt should be made to the Figures and Specification related either to consistency, spelling, syntax, or other grammatical matters and did not introduce any new matter. It is believed that these have now all been made.

Respectfully submitted,

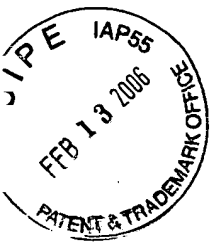


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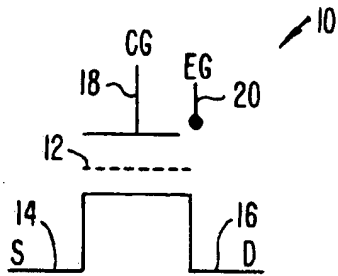


FIG. 1a.

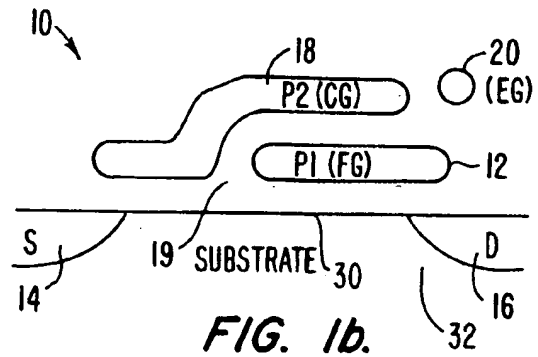


FIG. 1b.

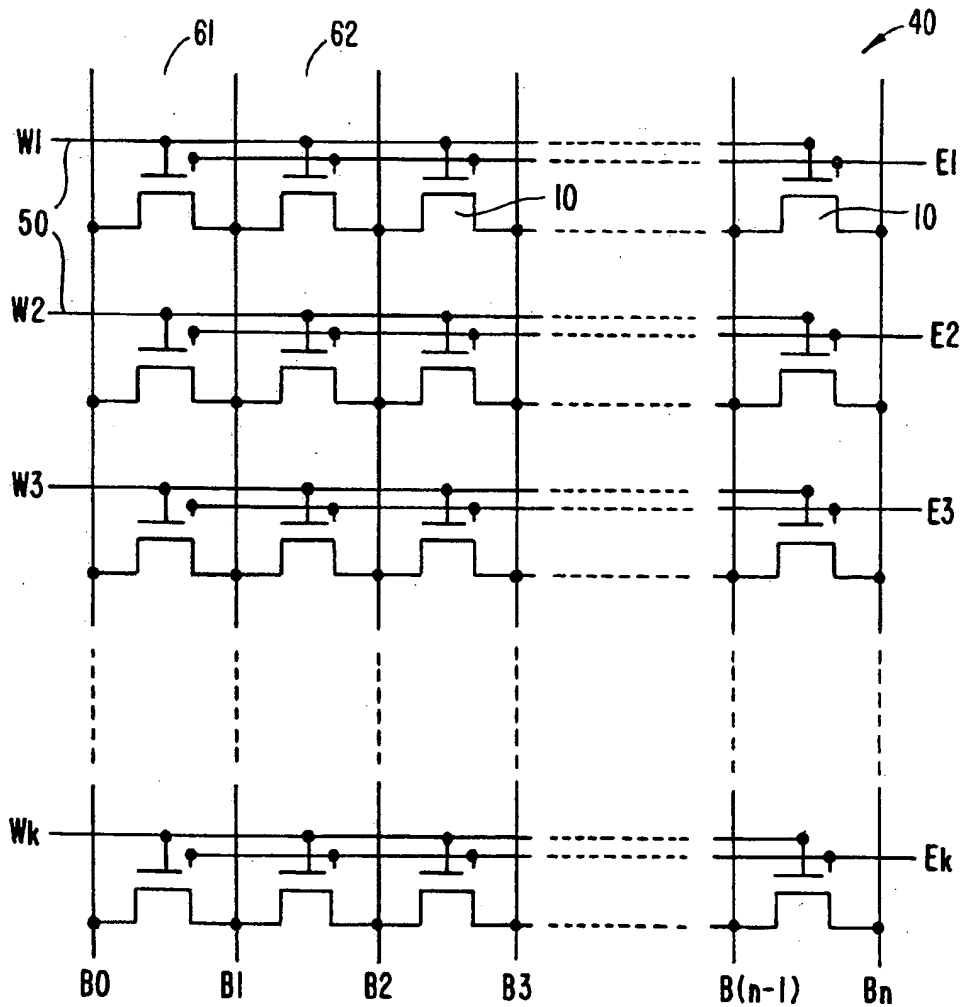


FIG. 2a

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VOLTAGE CONDITIONS FOR NORMAL MEMORY OPERATIONS

TYPE OF LINES	READ	PROGRAM	ERASE
SELECTED WORD LINE (WL)	5V	12V	0V
NON-SELECTED WORD LINE (WL)	0V	0V	0V
SELECTED SOURCE LINE (SL)	0V	0V	0V
SELECTED DRAIN LINE (DL)	1.5V	8V	0V
NON-SELECTED BIT LINES (BL)	FLOAT	FLOAT	0V
SELECTED ERASE LINE (EL)	0V	0V	20V
NON-SELECTED ERASE LINE (EL)	0V	0V	0V

FIG. 3.

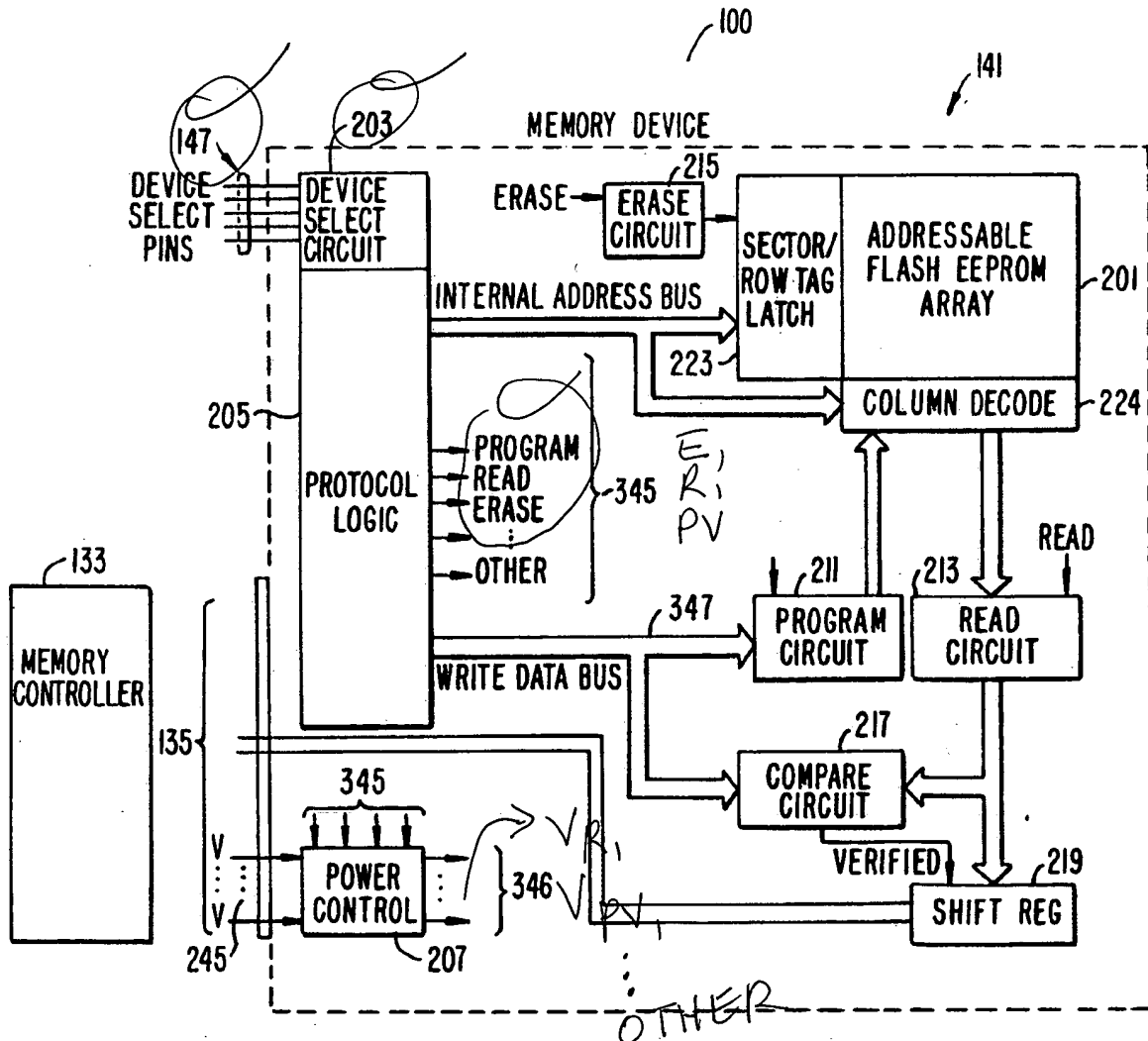


FIG. 4.

FIG. 6a.

